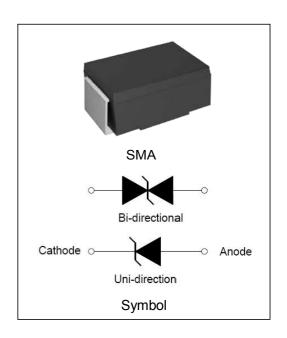


Transinet Voltage Suppression Diode

»Features

- Peak power dissipation 400W @10 x 1000 us Pulse
- Low profile package.
- Excellent clamping capability.
- Glass passivated junction.
- Fast response time: typically less than 1ps from 0 Volts to BV min
- IEC 61000-4-2 ESD 30KV(Air), 30KV(Contact)
- ESD protection of data lines in accordance with IEC 61000-4-2
- EFT protection of data lines in accordance with IEC 61000-4-4
- Halogen free and RoHS compliant
- Lead-free finish



»Mechanical Characteristics

- CASE: SMAJ (DO-214AC) Molded Plastic over glass passivated junction.
- Mounting Position: Any
- Polarity: by cathode band denotes uni-directional device, none cathode band denotes bi-directional device.
- Terminal: Solder plated

>> Maximum Ratings And Characteristics @ 25°C Ambient Temperature

Parameter	Symbol	Value	Units
Peak Pulse Power Dissipation on 10/1000 us Waveform (Note 1, 2, FIG.1)	P _{PPM}	Min 400	W
Power Dissipation on Infinite Heat Sink at T _L =50°C	P _D	3.3	W
Peak Pulse Current of on 10/1000us Waveform (Note 1, FIG.3)	I _{PPM}	See Table 1	Α
Peak Forward Surge Current, 8.3ms Single Half Sine-Wave (Note 2.3)	I _{FSM}	60	Α
Operating Junction Temperature Range	TJ	-55 to 150	°C
Storage Temperature Range	T _{STG}	-55 to 150	°C

Notes: 1. Non-repetitive current pulse, per Fig.3 and derated above T_A =25°C per Fig.2.

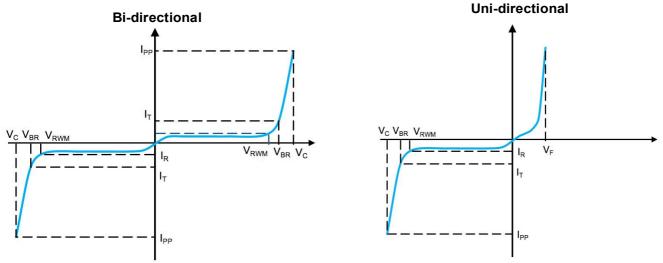
- 2. Mounted on 5.0x5.0mm² (0.03mm thick) Copper Pads to each terminal.
- 3. Measured on 8.3ms single half sine-wave, or equivalent square wave, for Unidirectional device only.

>> Electrical Specification @ Tamb 25°C

Type N	Number	Mark	ing	Reverse Stand-Off Voltage	Breakdown Voltage Min. @I _T	Breakdown Voltage Max. @ I _T	Test Current	Maximum Clamping Voltage @IPP	Peak Pulse Current	Reverse Leakage @V _{RMW}
(Uni)	(Bi)	(Uni)	(Bi)	V _{RMW} (V)	$V_{BR\ MIN}(V)$	V _{BR MAX} (V)	I _T (mA)	V _C (V)	$I_{PP}(A)$	I _R (uA)
SMAJ6.8A	SMAJ6.8CA	SMAJ 6.8A	SMAJ 6.8CA	5.8	6.45	7.14	10	10.5	39.5	500



»I-V Curve Characteristics



P_{PPM} Peak Pulse Power Dissipation - Max power dissipation

 \mathbf{V}_{RWM} Reverse Stand-off Voltage - Maximum voltage that can be applied to TVS without operation

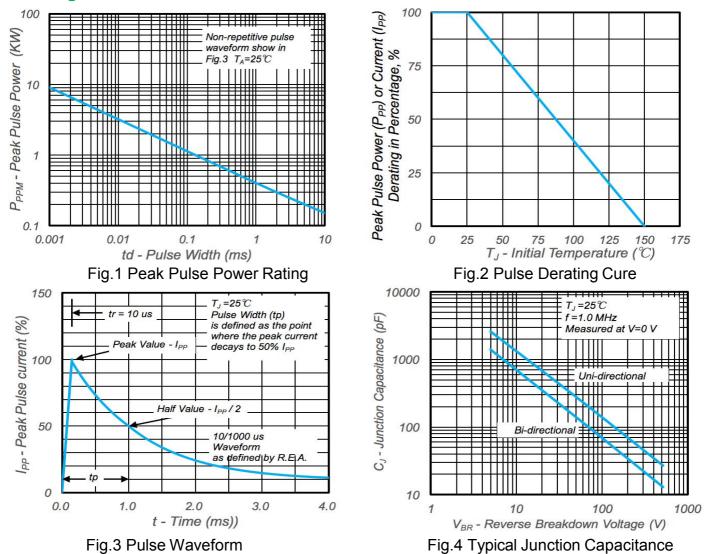
 V_{BR} Breakdown Voltage – Maximum voltage that flows though the TVS at a specified current (I_T)

Vc Clamping Voltage – Peak voltage measured across the TVS at a specified IPPM (peak impulse current)

 I_R Reverse Leakage Current – Current measured at V_R

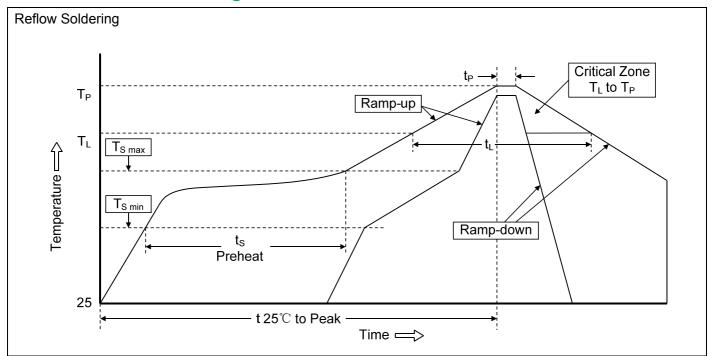
V_F Forward Voltage Drop for Uni-directional

>> Ratings and Characteristic Curves (TA=25°C unless otherwise noted)





»Recommended Soldering Conditions

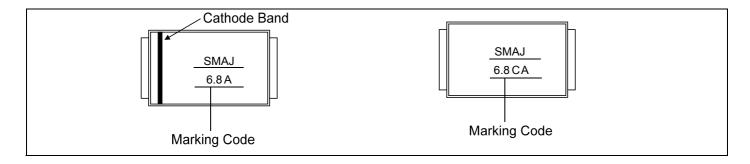


Recommended Conditions

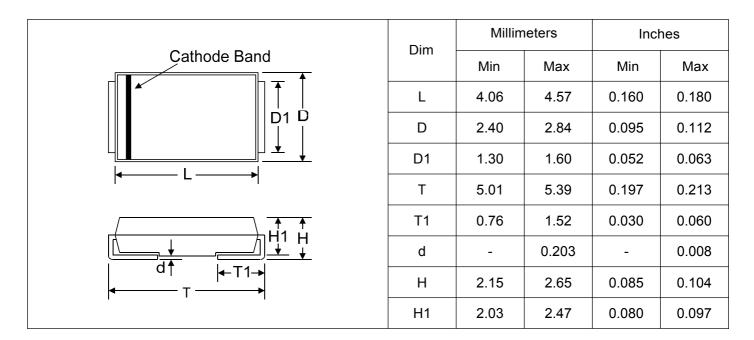
Profile Feature	Pb-Free Assembly			
Average ramp-up rate (T _L to T _P)	3°C/second max.			
Preheat -Temperature Min (T _{S min}) -Temperature Max (T _{S max}) -Time (min to max) (t _S)	150℃ 200℃ 60-180 seconds			
T _{S max} to T _L -Ramp-up Rate	3℃/second max.			
Time maintained above: -Temperature (T_L) -Time (t_L)	217°C 60-150 seconds			
Peak Temperature (T _P)	260℃			
Time within 5°C of actual Peak Temperature (t _P)	20-40 seconds			
Ramp-down Rate	6°C/second max.			
Time 25℃ to Peak Temperature	8 minutes max.			



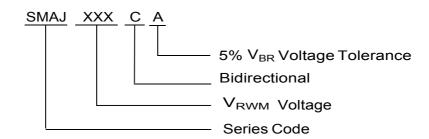
»Marking Code



>> Package Outline Dimensions and Pad Layouts (DO-214AC)



»Ordering Information





»Packaging

